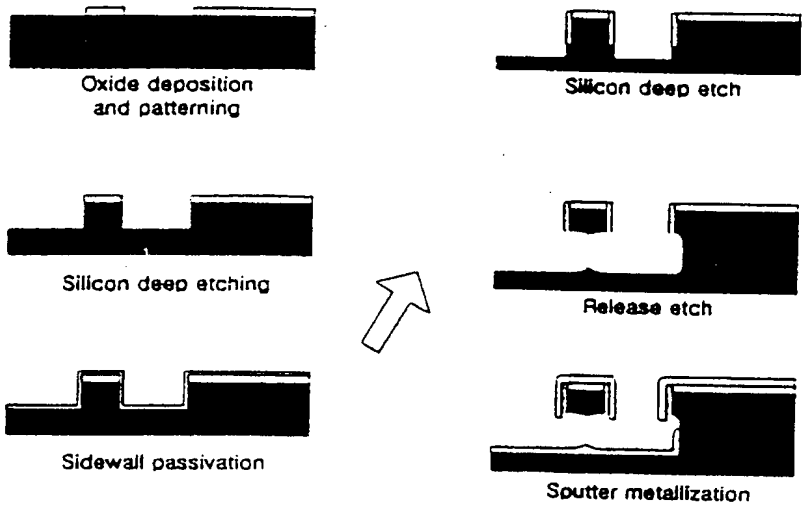


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FIG. 1



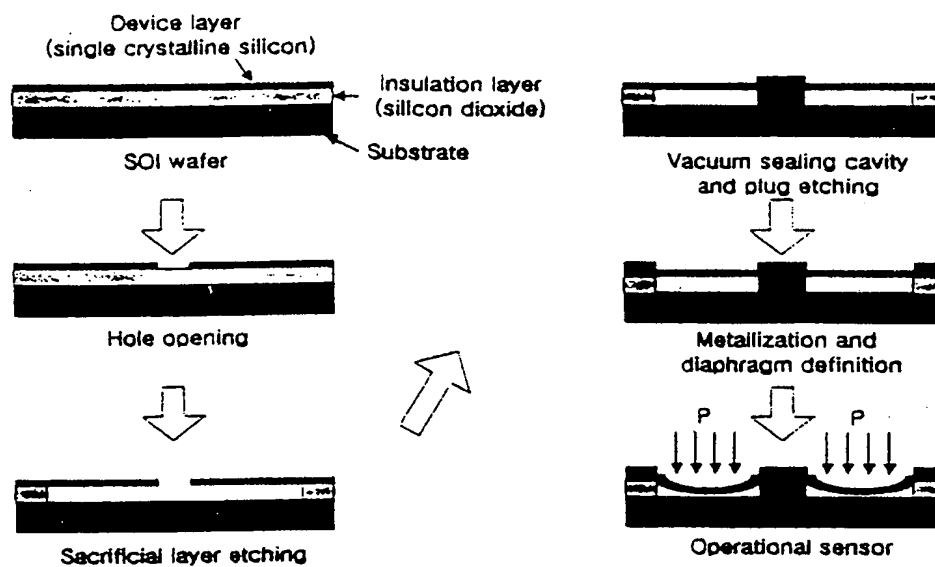
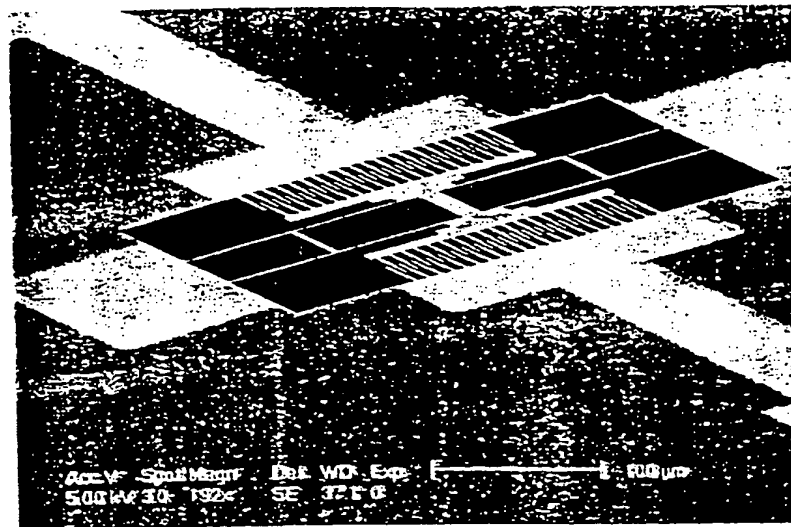
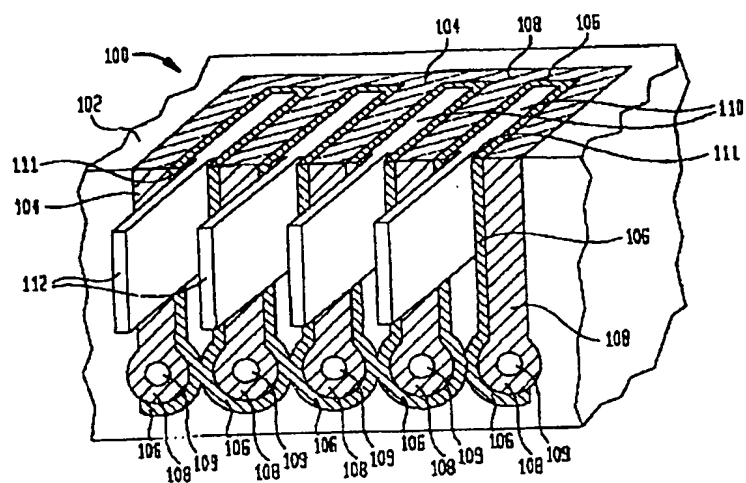
[illegible]

FIG. 3



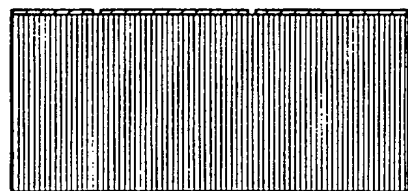
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FIG. 4

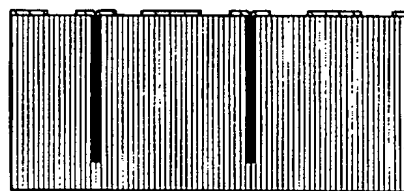


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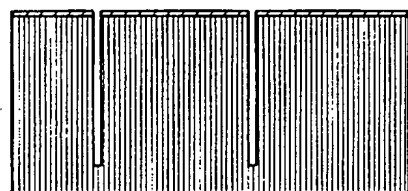
FIG. 5



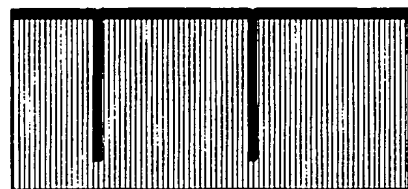
First etch mask deposition and patterning



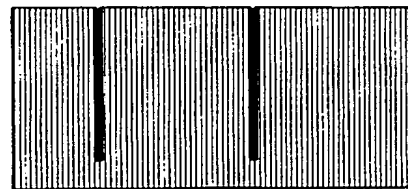
Second etch mask deposition and patterning



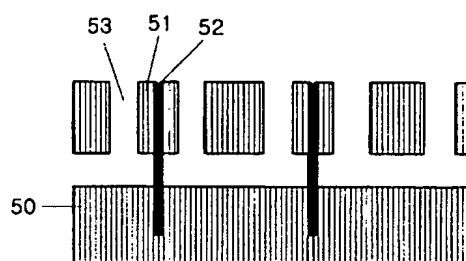
Deep silicon etching to form trenches



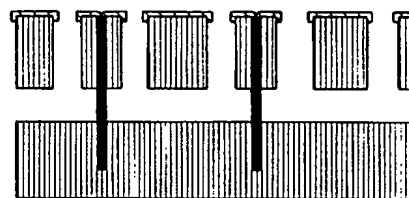
Trench filling by oxidation



Top oxide removal



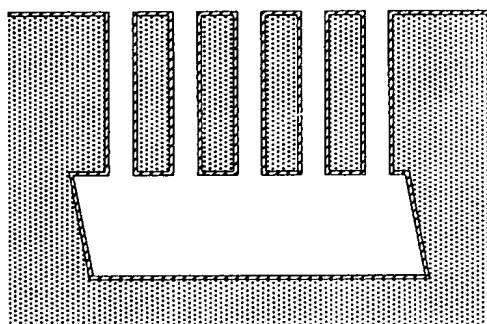
Structure fabrication



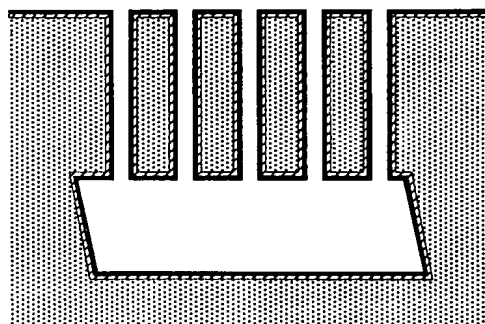
Metallization

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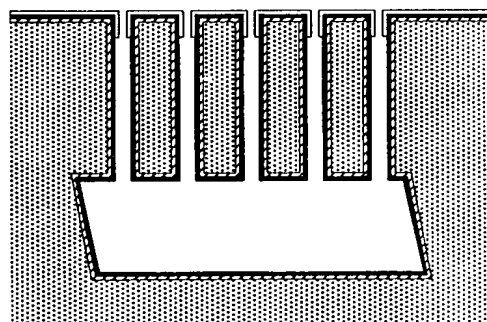
FIG. 6



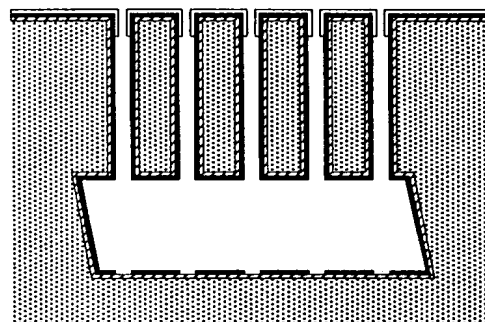
(a)



(b)



(c)

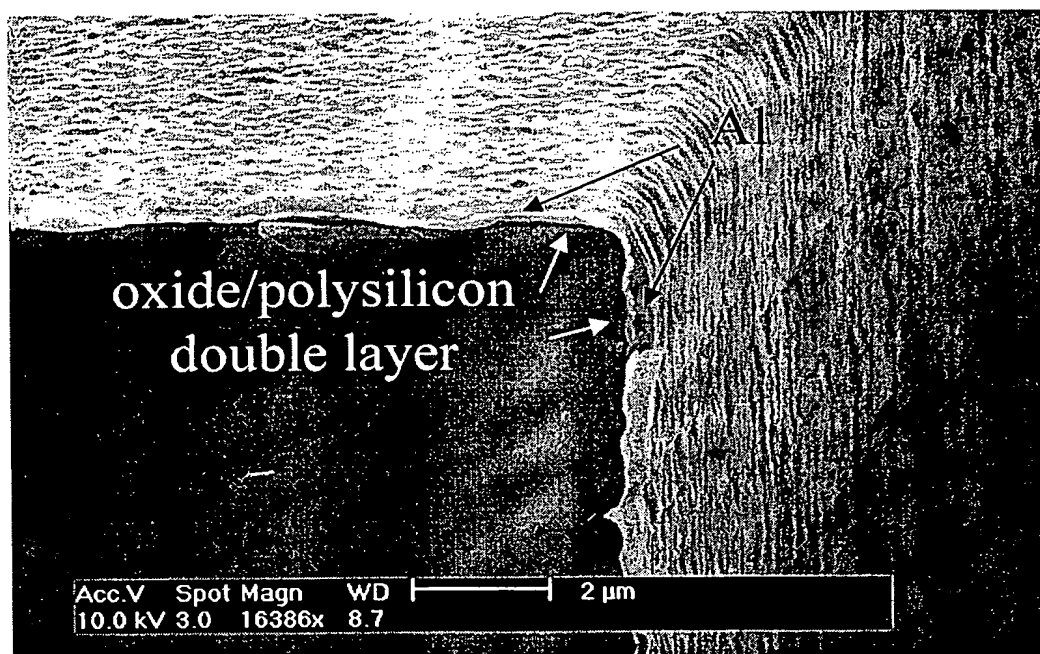


(d)

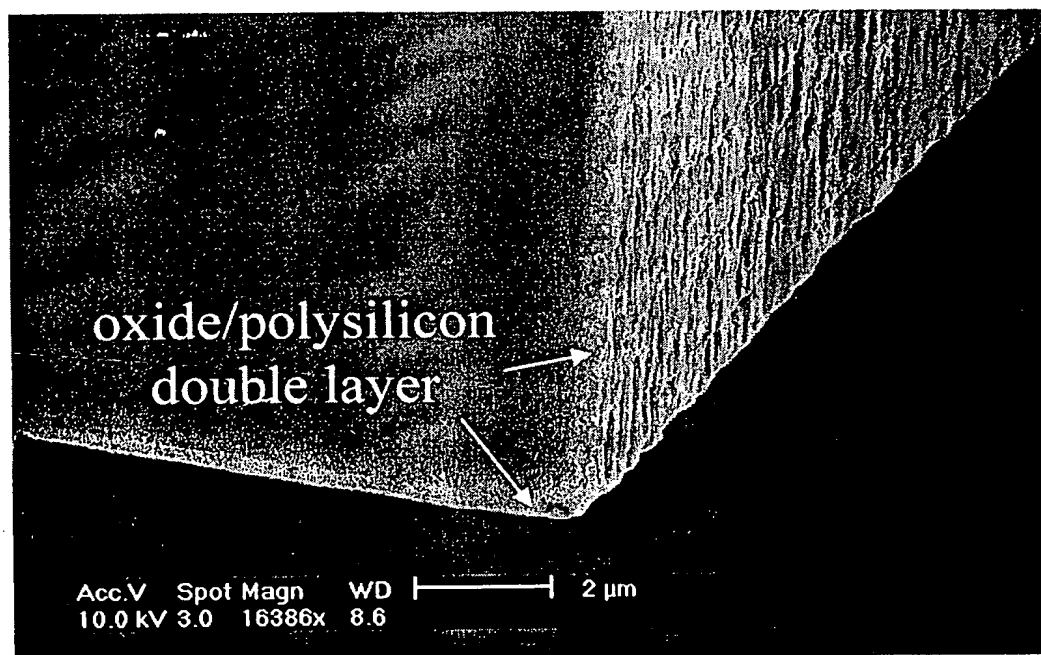


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FIG. 7

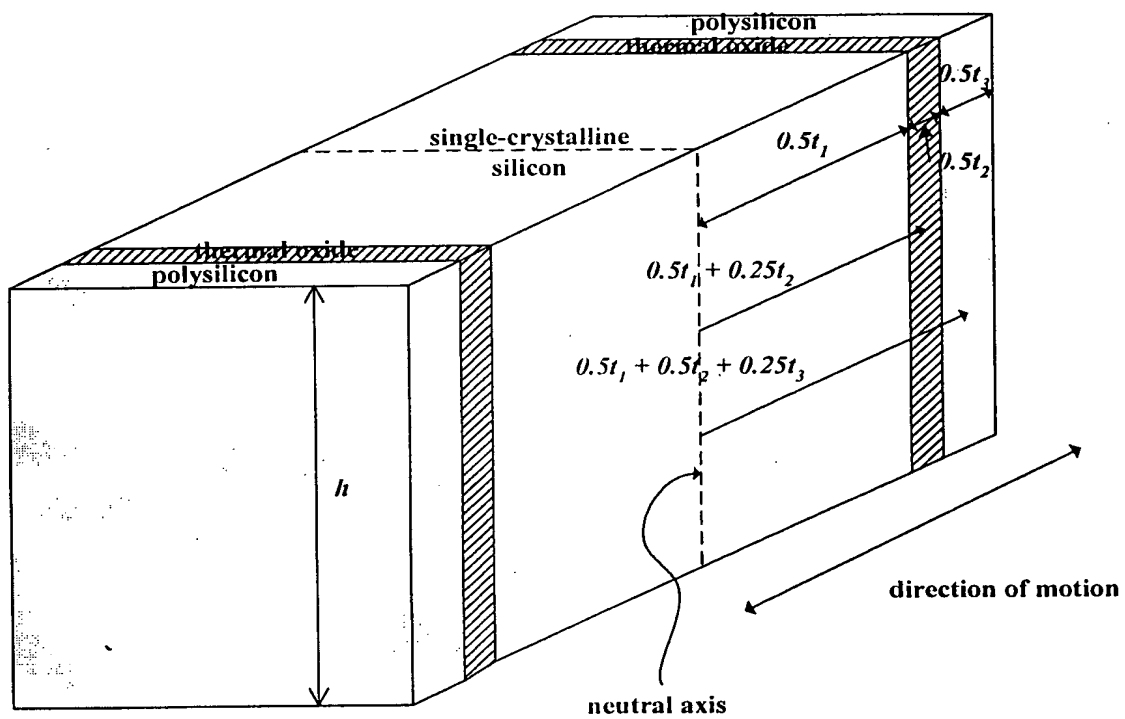


(a)



(b)

FIG. 8





[illegible]

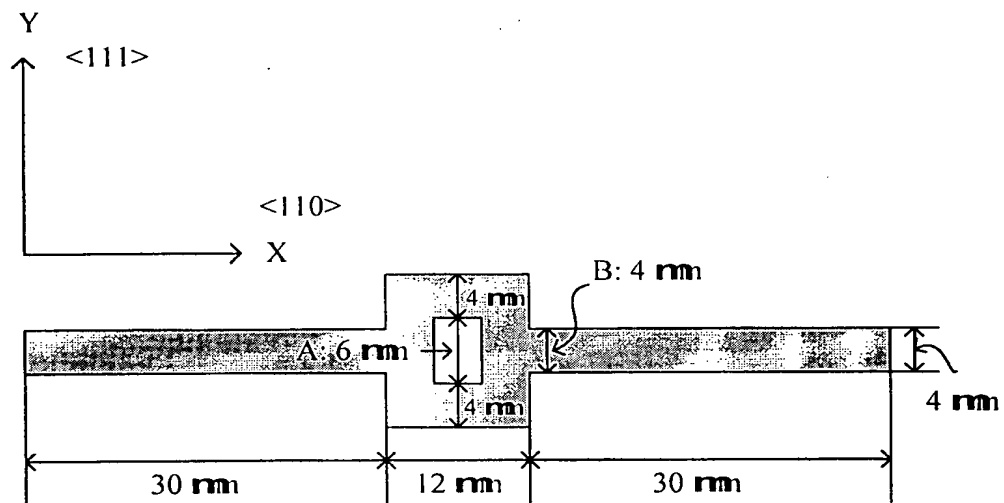


FIG. 11

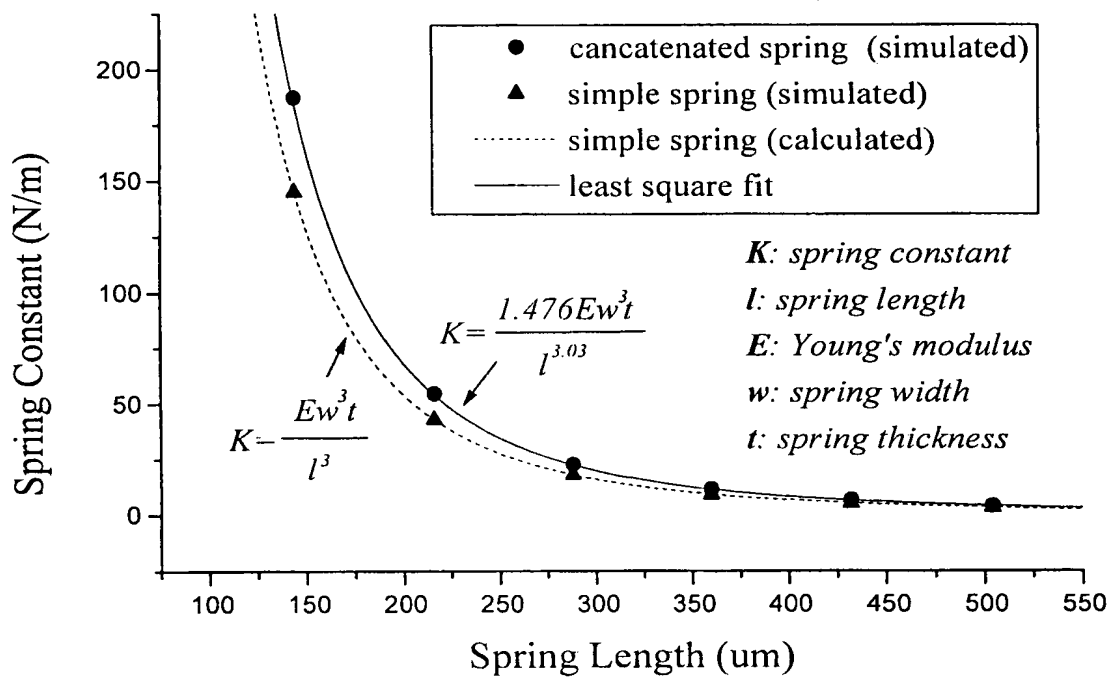
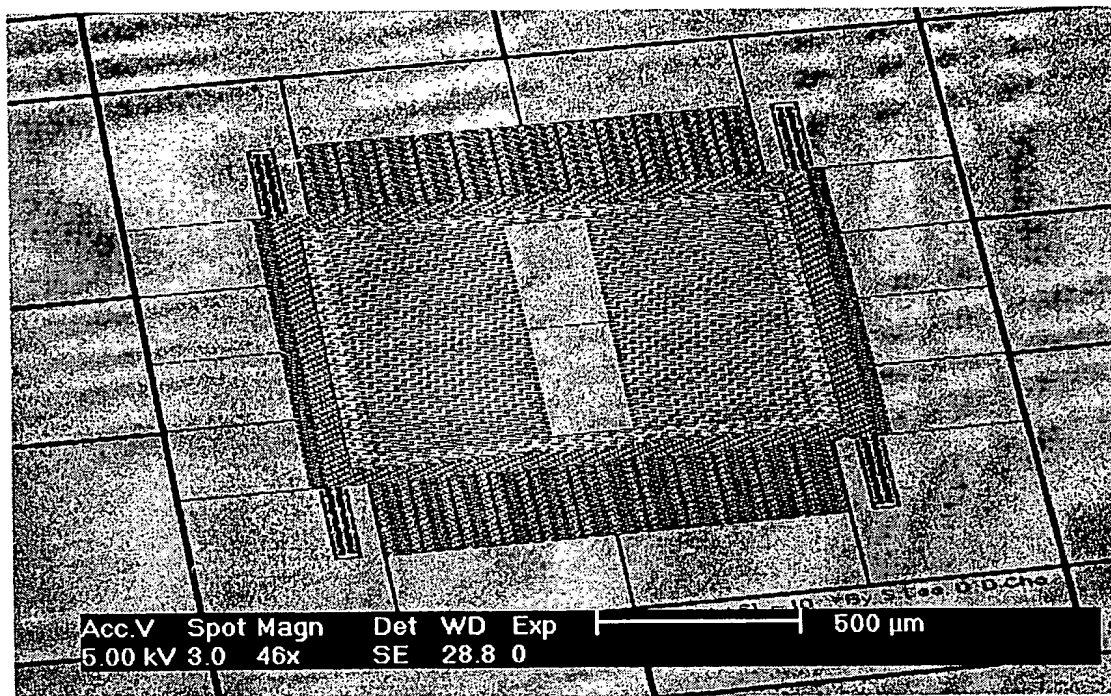
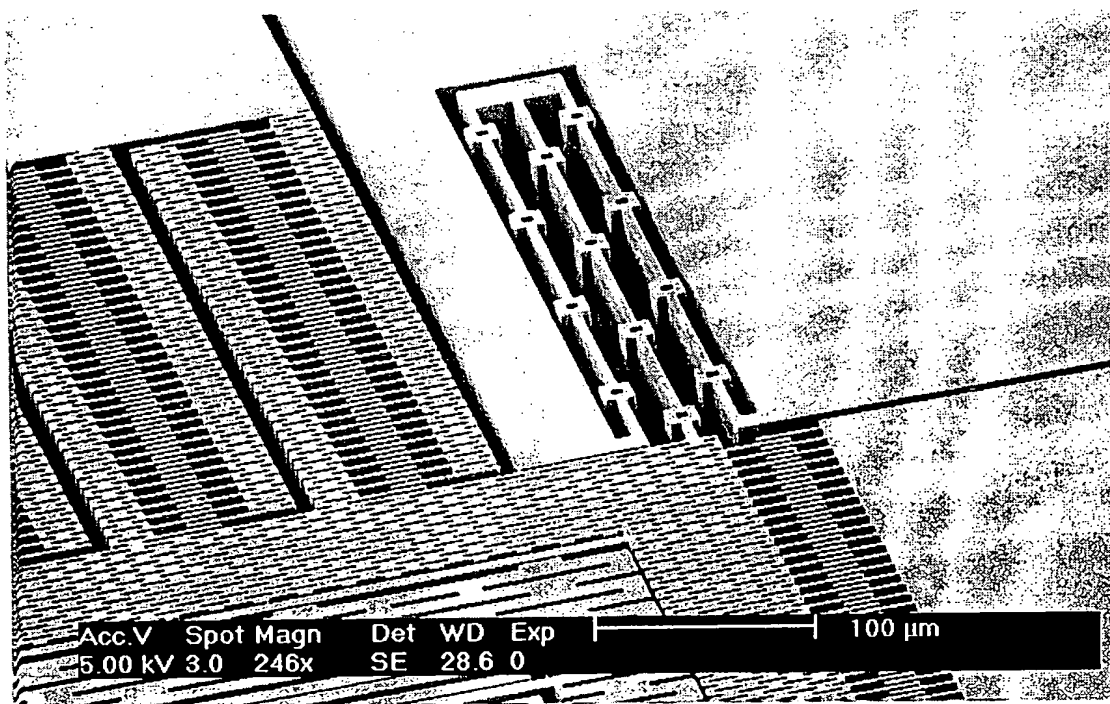


FIG. 12

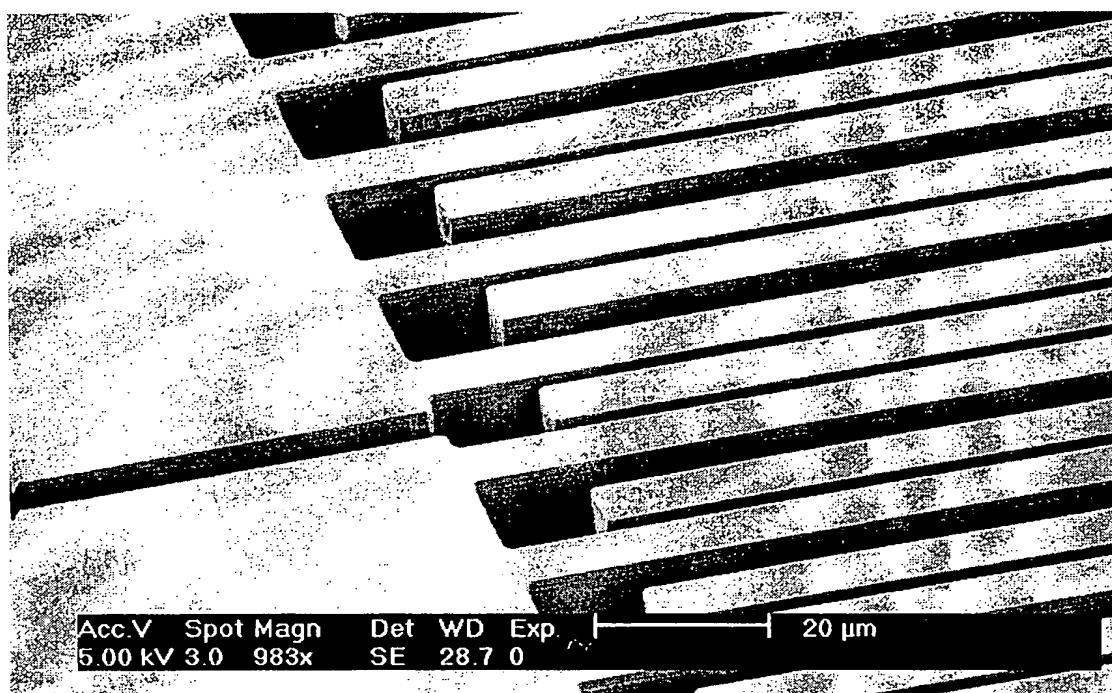


(a)

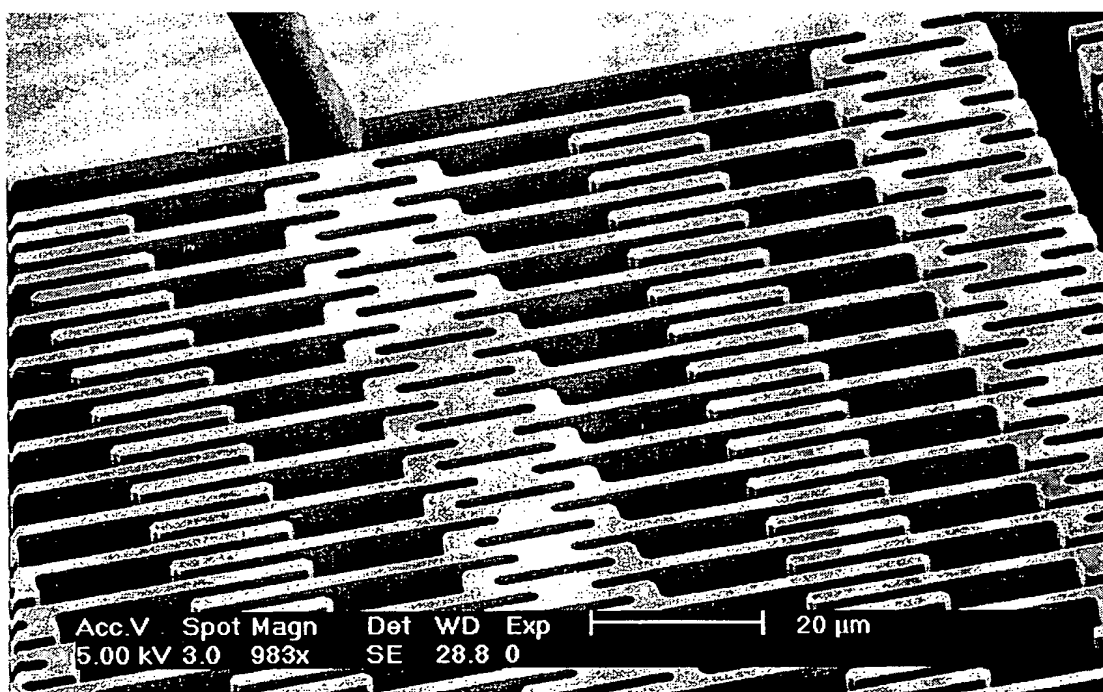


(b)

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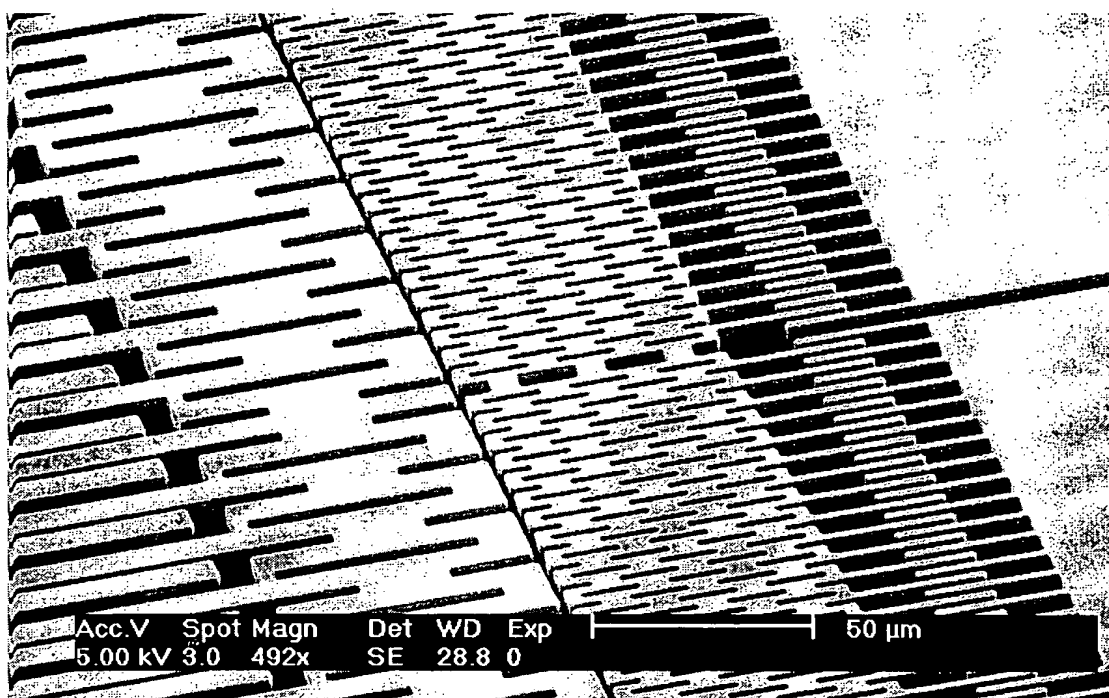


(c)



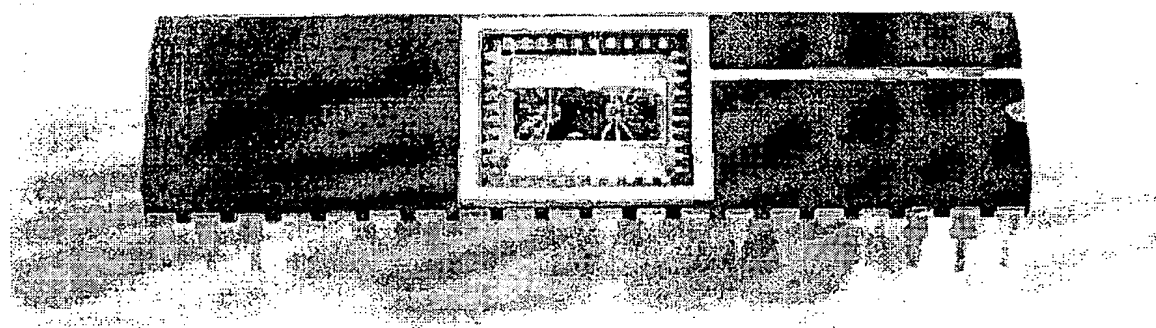
(d)

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(e)

FIG. 13



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FIG. 14

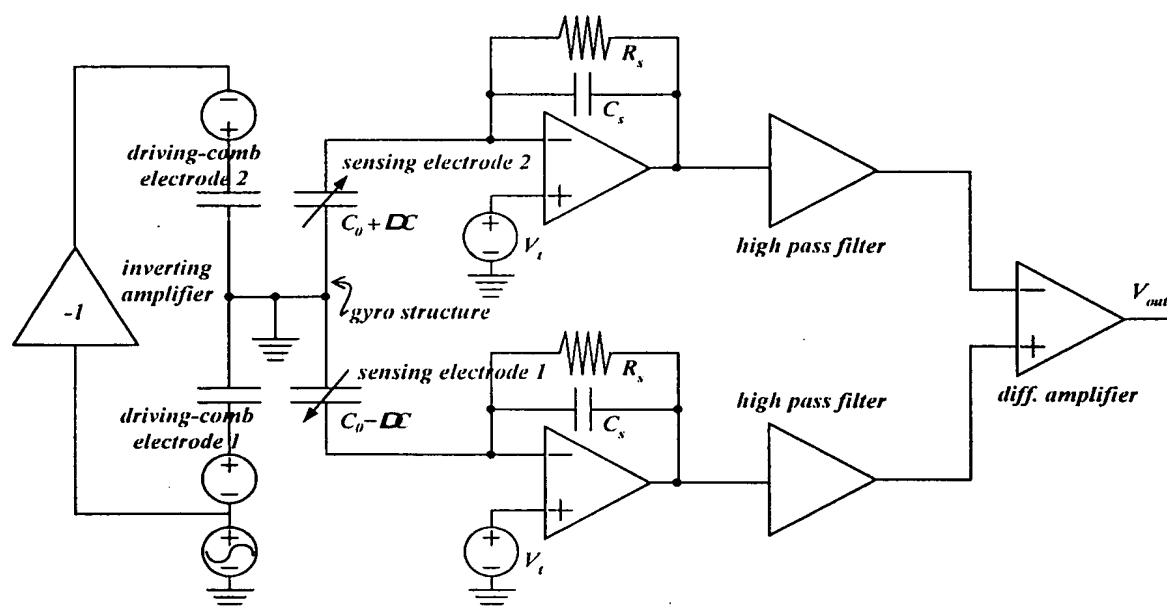
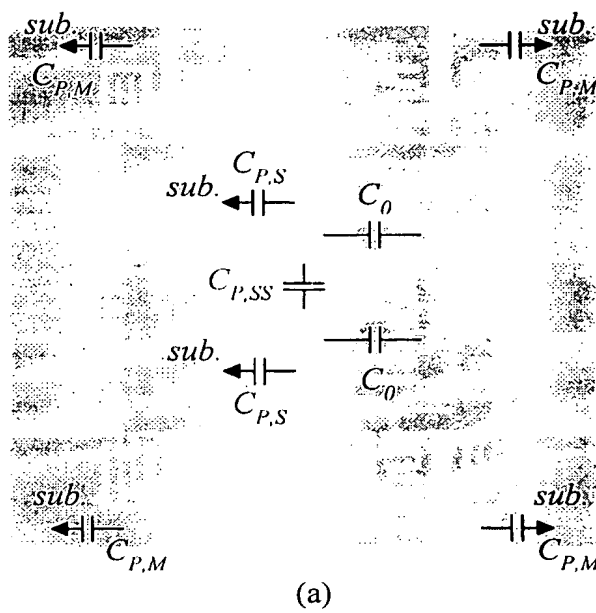
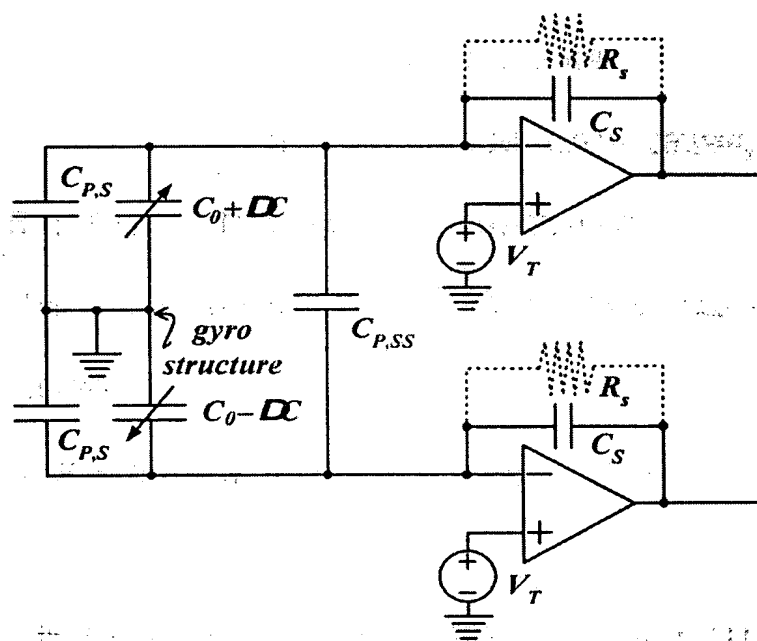




FIG. 15

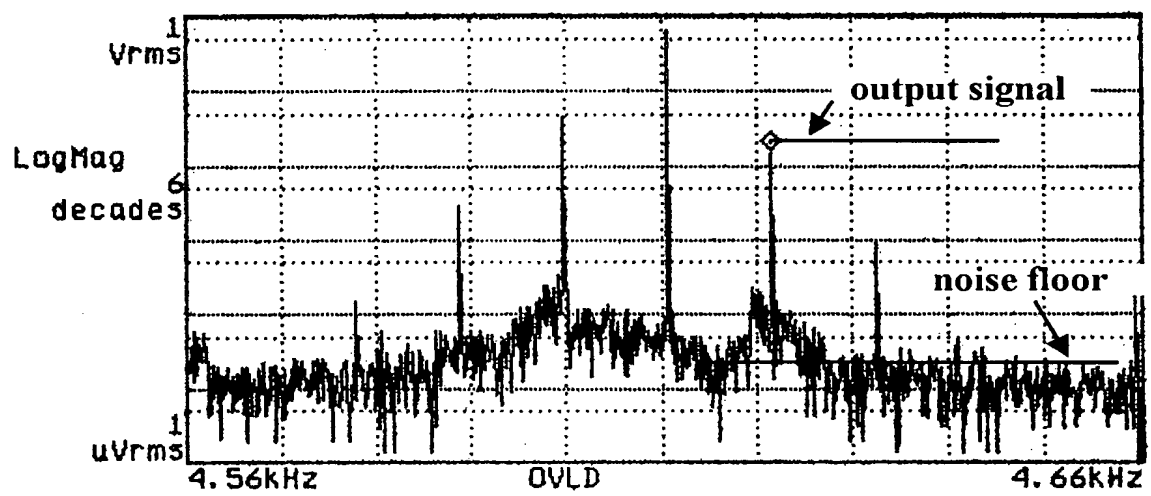


(a)



(b)

FIG. 16



(Y-axis corresponds to the root mean square voltage in Log-scale.)

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FIG. 17

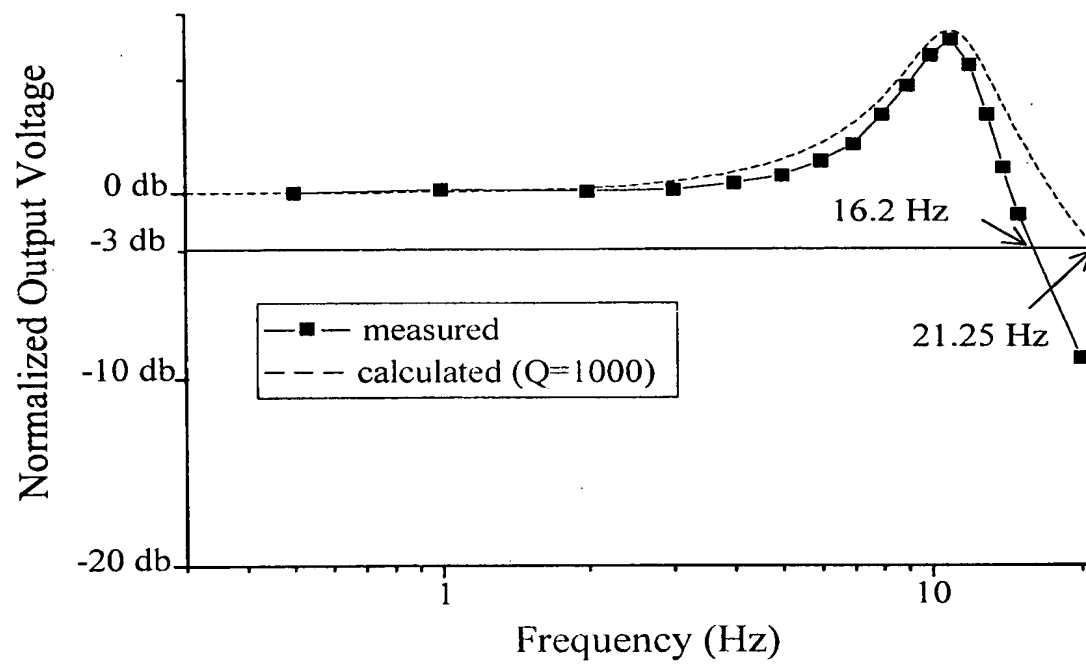
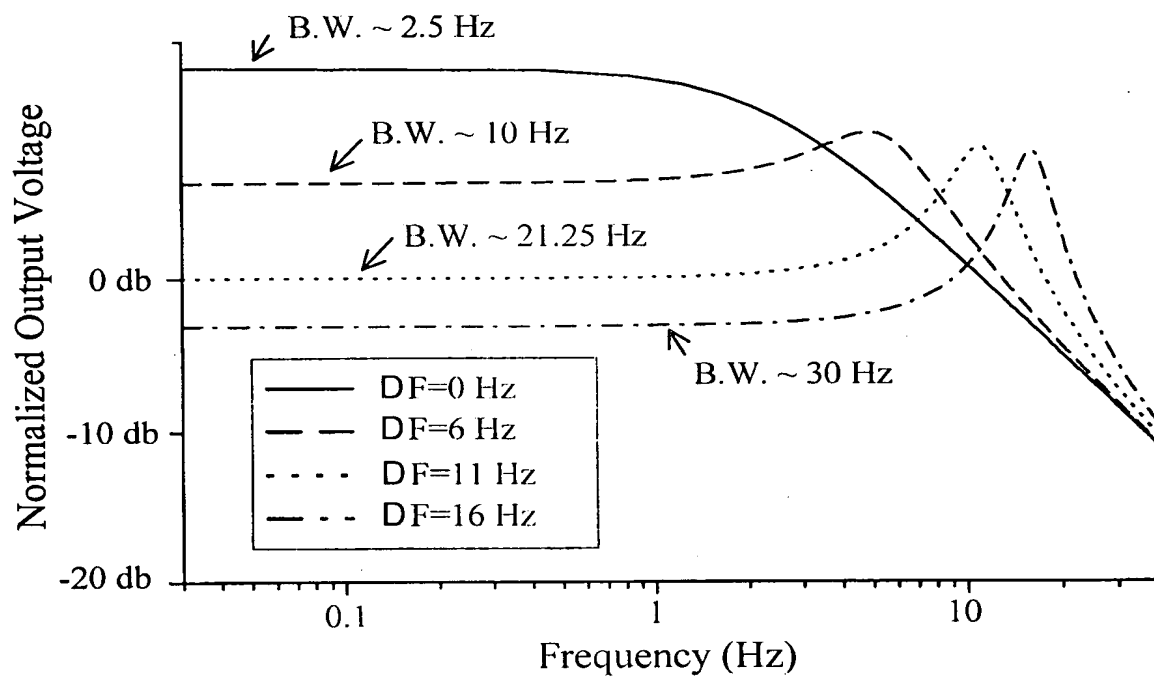


FIG. 18



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FIG. 19

